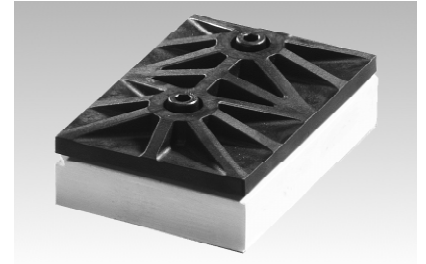


SKiiP 31 NAB 06

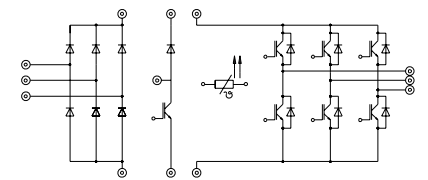
Absolute Maximum Ratings			
Symbol	Conditions ¹⁾	Values	Units
Inverter			
V_{CES}		600	V
V_{GES}		± 20	V
I_C	$T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	50 / 35	A
I_{CM}	$t_p < 1 \text{ ms}; T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	100 / 70	A
$I_F = -I_C$	$T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	57 / 38	A
$I_{FM} = -I_{CM}$	$t_p < 1 \text{ ms}; T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	114 / 76	A
Bridge Rectifier			
V_{RRM}		800	V
I_D	$T_{\text{heatsink}} = 80 \text{ }^\circ\text{C}$	25	A
I_{FSM}	$t_p = 10 \text{ ms}; \sin. 180^\circ; T_j = 25 \text{ }^\circ\text{C}$	370	A
I^2t	$t_p = 10 \text{ ms}; \sin. 180^\circ; T_j = 25 \text{ }^\circ\text{C}$	680	A ² s
T_j		- 40 ... + 150	$^\circ\text{C}$
T_{stg}		- 40 ... + 125	$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500	V

MiniSKiiP 3 SEMIKRON integrated intelligent Power SKiiP 31 NAB 06 3-phase bridge rectifier + braking chopper + 3-phase bridge inverter

Case M3



Characteristics					
Symbol	Conditions ¹⁾	min.	typ.	max.	Units
IGBT - Inverter					
V_{CESat}	$I_C = 50 \text{ A}; T_j = 25 (125) \text{ }^\circ\text{C}$	-	2,1(2,2)	2,7(2,8)	V
$t_{d(on)}$	$V_{CC} = 300 \text{ V}; V_{GE} = \pm 15 \text{ V}$ $I_C = 50 \text{ A}; T_j = 125 \text{ }^\circ\text{C}$ $R_{gon} = R_{goff} = 22 \text{ } \Omega$ inductive load	-	60	120	ns
t_r		-	80	160	ns
$t_{d(off)}$		-	330	500	ns
t_f		-	550	830	ns
$E_{on} + E_{off}$		-	7,3	-	mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}, 1 \text{ MHz}$	-	2,8	-	nF
R_{thjh}	per IGBT	-	-	1,0	K/W
IGBT - Chopper *					
V_{CESat}	$I_C = 30 \text{ A}; T_j = 25 (125) \text{ }^\circ\text{C}$	-	2,1(2,2)	2,7(2,8)	V
$t_{d(on)}$	$V_{CC} = 300 \text{ V}; V_{GE} = \pm 15 \text{ V}$ $I_C = 30 \text{ A}; T_j = 125 \text{ }^\circ\text{C}$ $R_{gon} = R_{goff} = 33 \text{ } \Omega$ inductive load	-	50	100	ns
t_r		-	80	160	ns
$t_{d(off)}$		-	250	370	ns
t_f		-	500	750	ns
$E_{on} + E_{off}$		-	4,0	-	mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}, 1 \text{ MHz}$	-	1,6	-	nF
R_{thjh}	per IGBT	-	-	1,7	K/W
Diode ²⁾ - Inverter & Chopper					
$V_F = V_{EC}$	$I_F = 50 \text{ A}; T_j = 25 (125) \text{ }^\circ\text{C}$	-	1,45(1,4)	1,7(1,7)	V
V_{TO}	$T_j = 125 \text{ }^\circ\text{C}$	-	0,85	0,9	V
r_T	$T_j = 125 \text{ }^\circ\text{C}$	-	11	16	m Ω
I_{RRM}	$I_F = 50 \text{ A}, V_R = -300 \text{ V}$ $di_F/dt = -800 \text{ A}/\mu\text{s}$ $V_{GE} = 0 \text{ V}, T_j = 125 \text{ }^\circ\text{C}$	-	50	-	A
Q_{rr}		-	5,0	-	μC
E_{off}		-	1,5	-	mJ
R_{thjh}		per diode	-	-	1,2
Diode - Rectifier					
V_F	$I_F = 25 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$	-	1,2	-	V
R_{thjh}	per diode	-	-	2,6	K/W
Temperature Sensor					
R_{TS}	$T = 25 / 100 \text{ }^\circ\text{C}$		1000 / 1670		Ω
Mechanical Data					
M_1	case to heatsink, SI Units	2	-	2,5	Nm
Case	mechanical outline see page B 16 - 9		M3		



UL recognized file no. E63532

- specification of temperature sensor see part A
- common characteristics see page B16-3

Options

- also available with faster IGBTs (type ... 063), data sheet on request

¹⁾ $T_{\text{heatsink}} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

²⁾ CAL = Controlled Axial Lifetime Technology (soft and fast recovery)

* For diagrams of the Chopper IGBT please refer to SKiiP 22 NAB 06

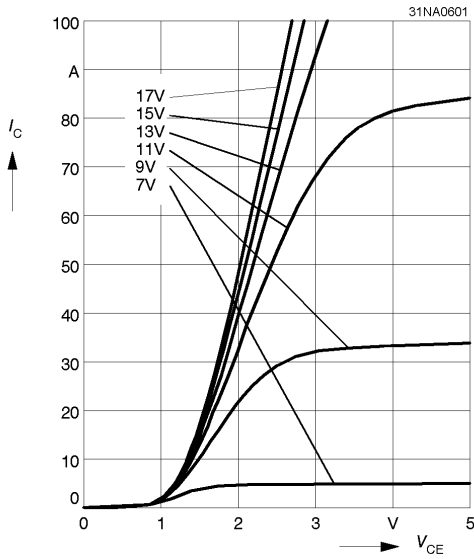


Fig. 1 Typ. output characteristic, $t_p = 80 \mu s$; $25 \text{ }^\circ\text{C}$

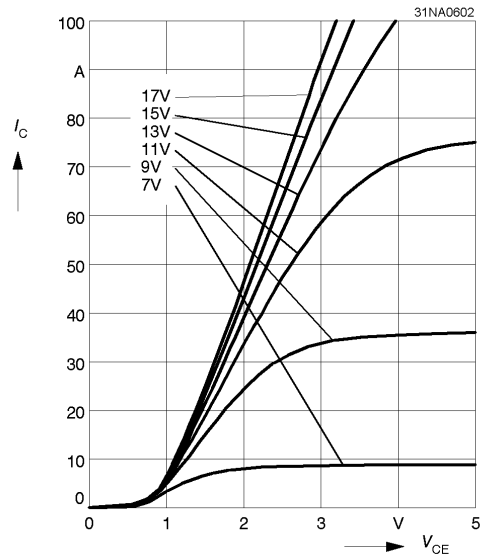


Fig. 2 Typ. output characteristic, $t_p = 80 \mu s$; $125 \text{ }^\circ\text{C}$

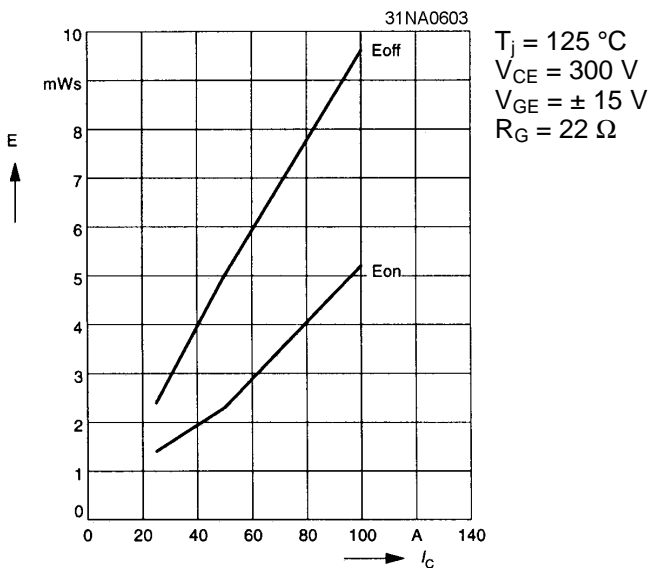


Fig. 3 Turn-on /-off energy = $f(I_c)$

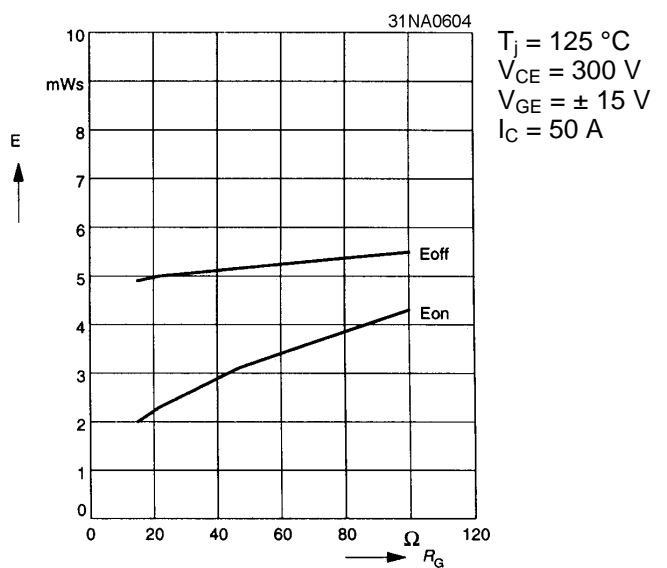


Fig. 4 Turn-on /-off energy = $f(R_G)$

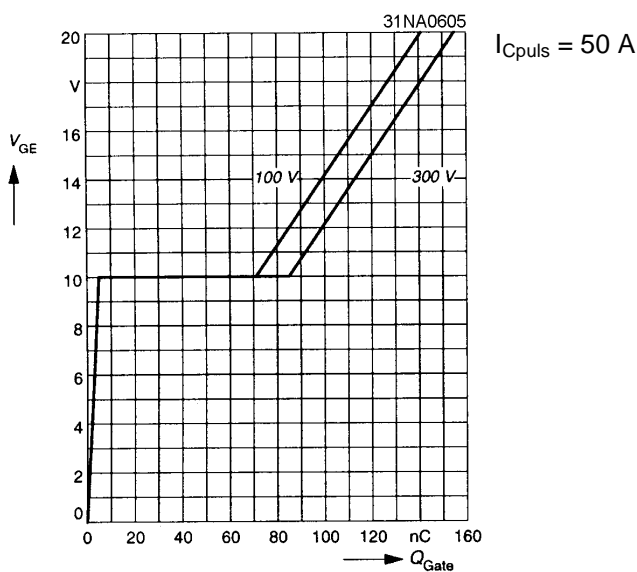


Fig. 5 Typ. gate charge characteristic

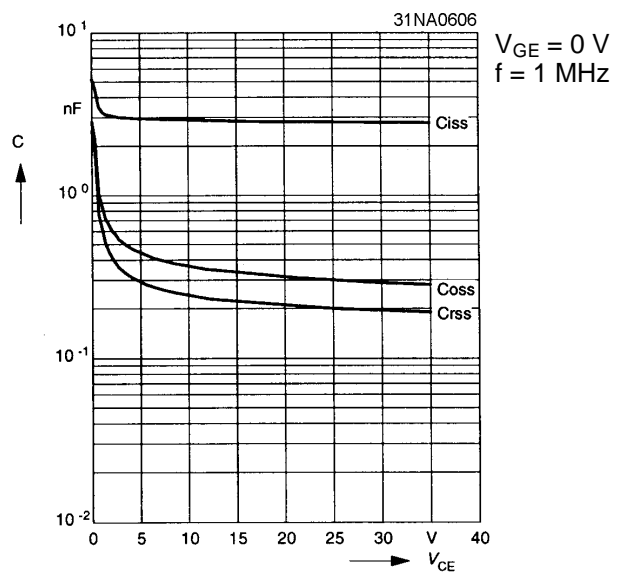


Fig. 6 Typ. capacitances vs. V_{CE}

2. Common characteristics of MiniSKiiP

MiniSKiiP 600 V

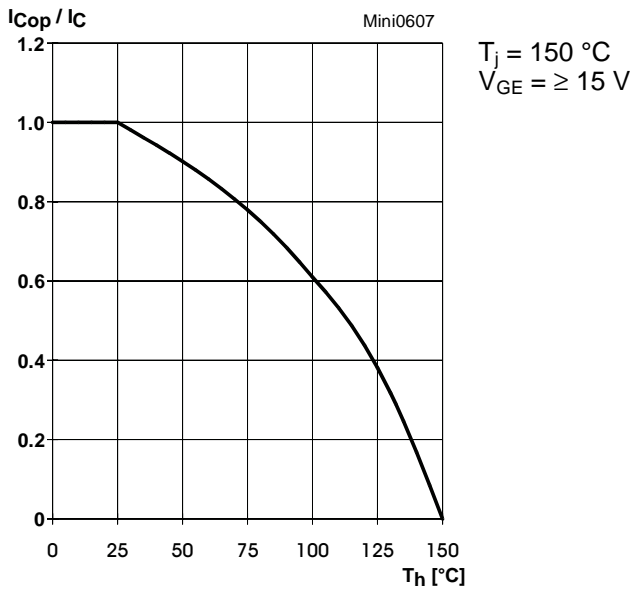


Fig. 7 Rated current of the IGBT $I_{COP} / I_C = f(T_h)$

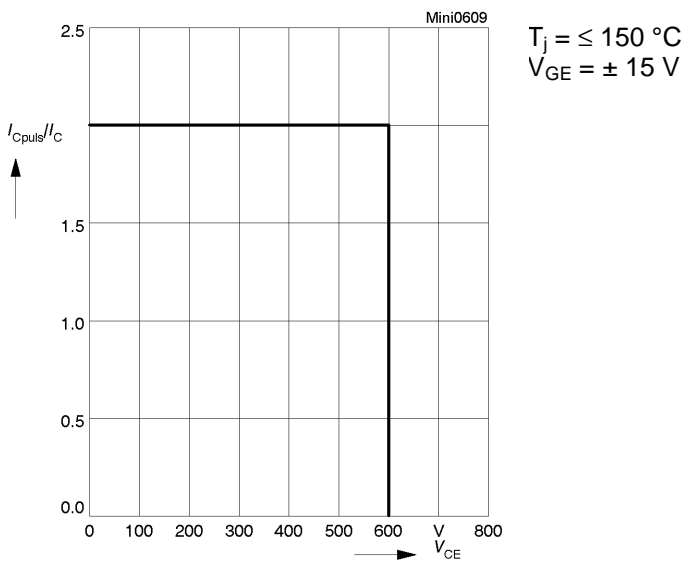


Fig. 9 Turn-off safe operating area (RBSOA) of the IGBT

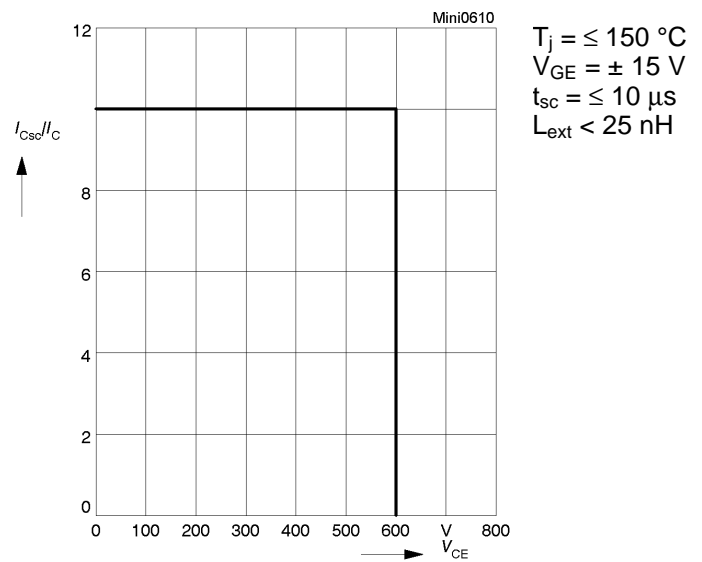


Fig. 10 Safe operating area at short circuit of the IGBT

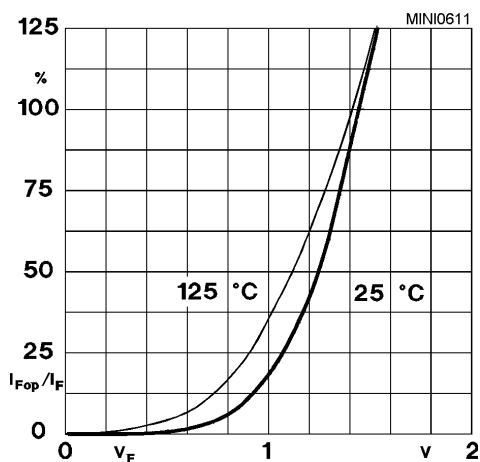


Fig. 11 Typ. freewheeling diode forward characteristic

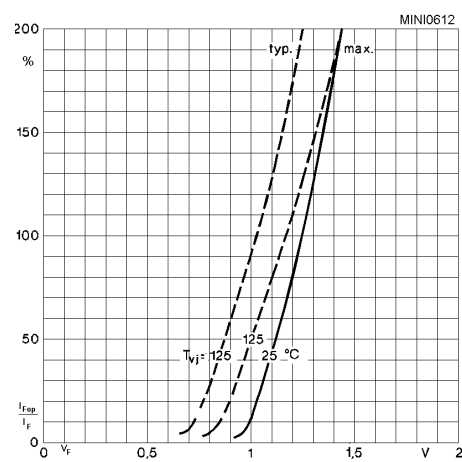


Fig. 12 Forward characteristic of the input bridge diode

